HYG350C06LA1S

Absolute Maximum Ratings

Symbol	Parameter		N-Channel	P-Channel	Unit
Common Ratings (Tc=25℃ Unless Otherwise Noted)					
V_{DSS}	Drain-Source Voltage		60	-60	V
V_{GSS}	Gate-Source Voltage		±20		V
T_J	Junction Temperature Range		-55 to 175		℃
T_{STG}	Storage Temperature Range				℃
I_S	Source Current-Continuous(Body Diode)	Tc=25°C	6.3	-4.8	A
Mounted on Large Heat Sink					
I_{DM}	Pulsed Drain Current *	Tc=25°C	25	-20	A
I_D	Continuous Drain Current	Tc=25°C	6.3	-4.8	A
		Tc=100°C	4.4	-3.4	A
P_D	Maximum Power Dissipation	Tc=25°C	3		W
		Tc=100°C	1.5		W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient **		50		°C/W
E_{AS}	Single Pulsed-Avalanche Energy ***	L=0.3mH	30	35	mJ

Note: * Repetitive rating；pulse width limited by max.junction temperature.
** Surface mounted on 1in2 FR-4 board.
*** Limited by $T_J$max , starting T_J=25°C, L = 0.3mH, R_G= 25Ω, V_{GS} =10V (N-Channel) / V_{GS} =-10V (P-Channel).

HYG350C06LA1S

N-Mosfet Typical Operating Characteristics

Figure 1: Power Dissipation

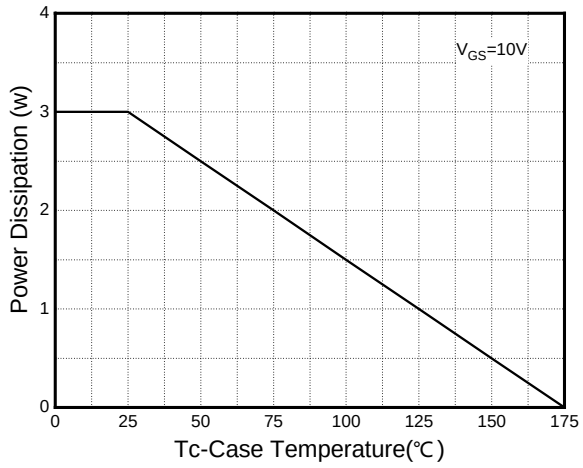


Figure 2: Drain Current

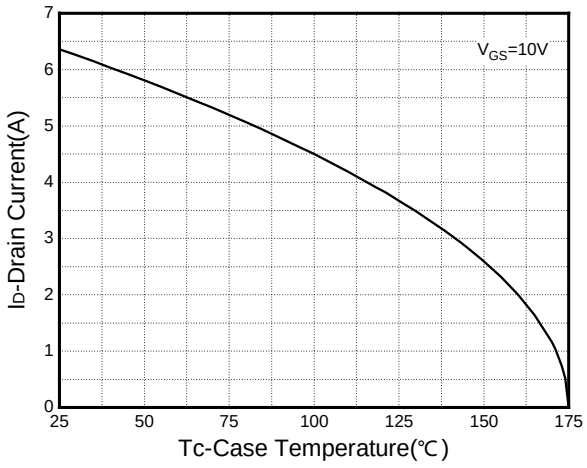


Figure 3: Safe Operation Area

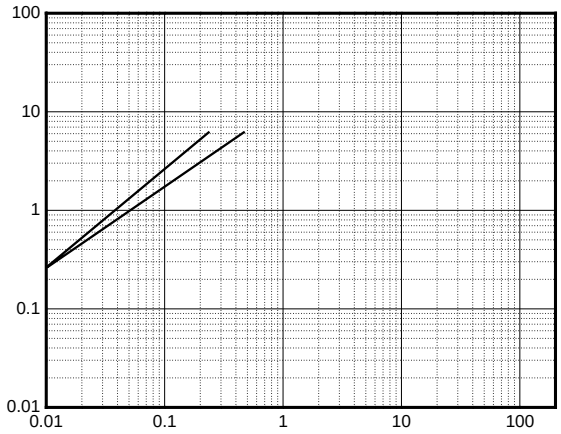


Figure 4: Thermal Transient Impedance

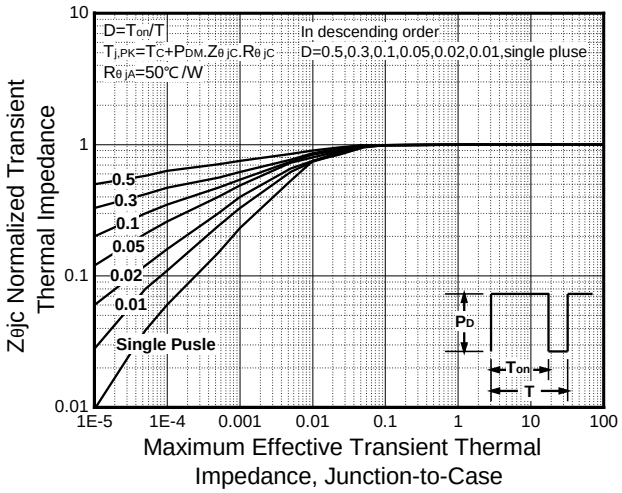


Figure 5: Output Characteristics

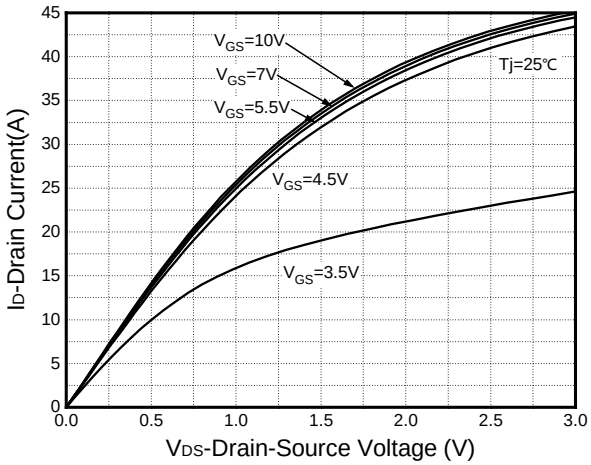
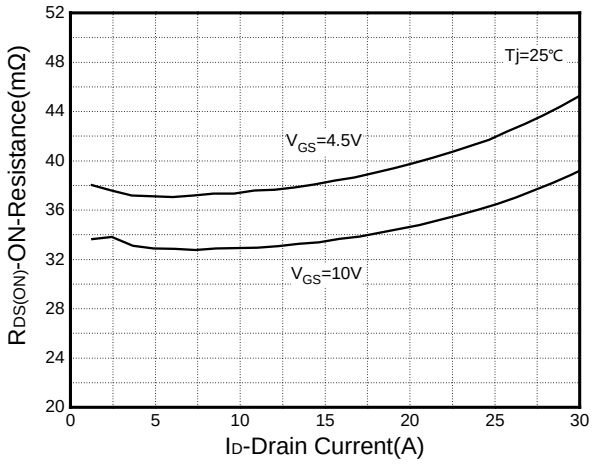


Figure 6: Drain-Source On Resistance



N-Mosfet Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

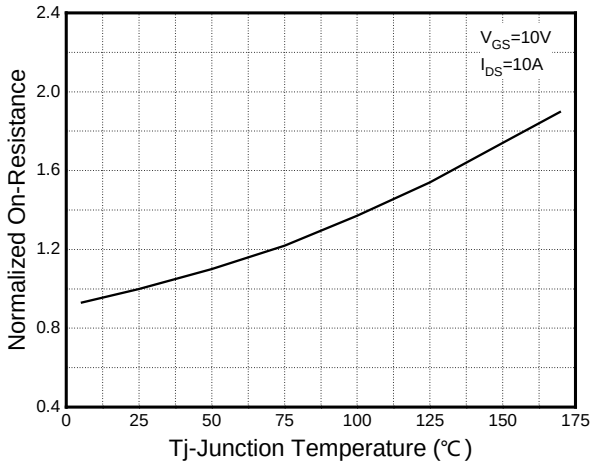


Figure 8: Source-Drain Diode Forward

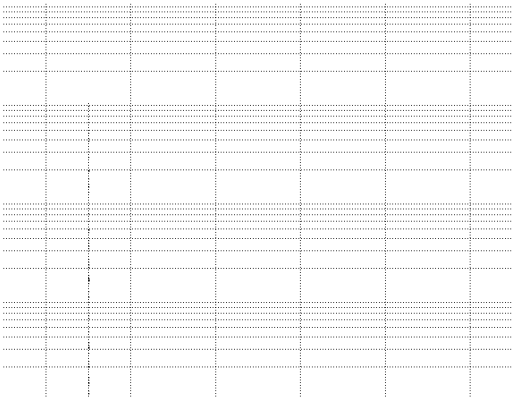


Figure 9: Capacitance Characteristics

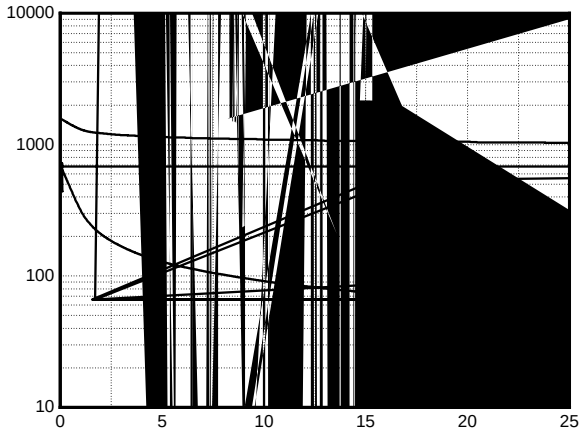
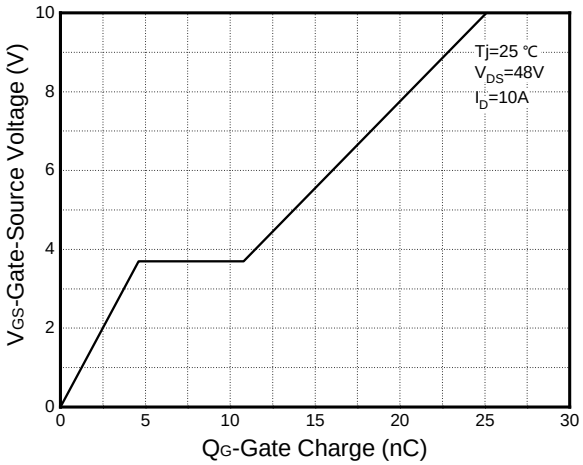


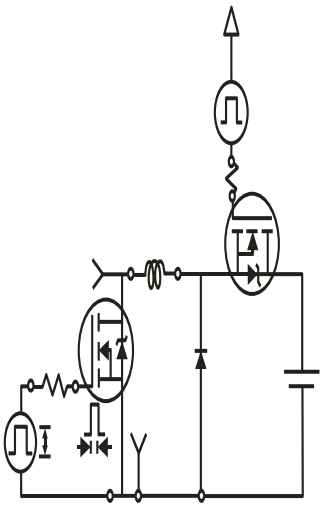
Figure 10: Gate Charge Characteristics



N-Mosfet Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

Figure 8: Source-Drain Diode Forward



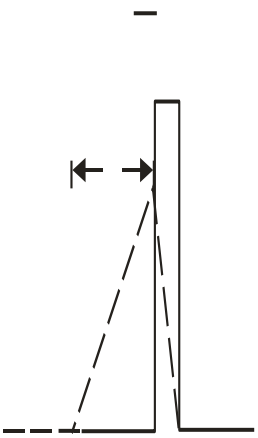


Figure 9: Capacitance Characteristics

Figure 10: Gate Charge Characteristics